

## 1. General description

Planar passivated SCR with sensitive gate in surface mountable plastic package and through-hole package. This SCR is designed to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

## 2. Features and benefits

- On-state RMS current, 1.25 A
- Repetitive peak off-state voltage, 1250 V
- High surge current capability
- Direct triggering from low power drivers and logic ICs
- Planar passivated for voltage ruggedness and reliability
- Surface mountable package (SOT223)
- Through-hole package (TO92)

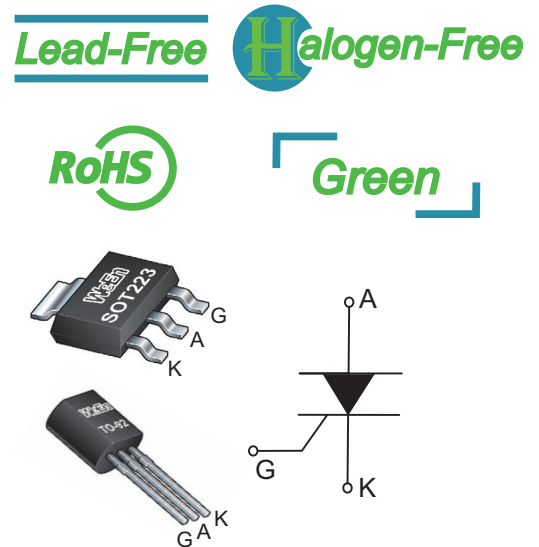
## 3. Applications

- GFCI (Ground Fault Circuit Interrupter)
- AFCI (Arc Fault Circuit Interrupter)
- RCD (Residual Current Device)
- RCBO (Residual Current circuit Breaker with Overload protection)
- AFDD (Arc Fault Detection Device)

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Values	Unit
$V_{DRM}, V_{RRM}$	1250	V
$I_{T(RMS)}$	1.25	A
$I_{GT}$	$\leq 90$	$\mu A$
$T_j$	125	$^{\circ}C$



## 5. Characteristics

**Table 2. Limiting values**
*In accordance with the Absolute Maximum Rating System (IEC 60134).*

Symbol	Parameter	Conditions	Values	Unit
$V_{DRM}$	repetitive peak off-state voltage	$R_{GK} = 1 \text{ k}\Omega$ ; $T_{j(\text{init})} = 25 \text{ }^\circ\text{C}$	1250	V
$V_{RRM}$	repetitive peak reverse voltage	$R_{GK} = 1 \text{ k}\Omega$ ; $T_{j(\text{init})} = 25 \text{ }^\circ\text{C}$	1250	V
$I_{T(AV)}$	average on-state current	half sine wave $T_{\text{lead}} \leq 83 \text{ }^\circ\text{C}$ $T_c \leq 110 \text{ }^\circ\text{C}$	0.8	A
		TO92 SOT223		
$I_{T(RMS)}$	RMS on-state current	half sine wave $T_{\text{lead}} \leq 83 \text{ }^\circ\text{C}$ $T_c \leq 110 \text{ }^\circ\text{C}$	1.25	A
		TO92 SOT223		
$I_{TSM}$	non-repetitive peak on-state current	half sine wave; $T_{j(\text{init})} = 25 \text{ }^\circ\text{C}$ ; $t_p = 10 \text{ ms}$	20	A
		half sine wave; $T_{j(\text{init})} = 25 \text{ }^\circ\text{C}$ ; $t_p = 8.3 \text{ ms}$	22	A
$I^2t$	$I^2t$ for fusing	$t_p = 10 \text{ ms}$ ; sine-wave pulse	2	$\text{A}^2\text{s}$
$di_T/dt$	rate of rise of on-state current	$I_G = 0.2 \text{ mA}$	100	$\text{A}/\mu\text{s}$
$I_{GM}$	peak gate current		1.2	A
$P_{GM}$	peak gate power		2	W
$P_{G(AV)}$	average gate power	over any 20 ms period	0.2	W
$T_{stg}$	storage temperature		-40 to 150	$^\circ\text{C}$
$T_j$	junction temperature		-40 to 125	$^\circ\text{C}$

**Table 3. Electrical Characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12 \text{ V}$ ; $R_L = 100 \text{ }\Omega$ ; $T_j = 25 \text{ }^\circ\text{C}$	10	-	90	$\mu\text{A}$
$V_{GT}$	gate trigger voltage	$V_D = 12 \text{ V}$ ; $R_L = 100 \text{ }\Omega$ ; $T_j = 25 \text{ }^\circ\text{C}$	-	0.6	0.8	V
		$V_D = 800 \text{ V}$ ; $I_T = 0.1 \text{ A}$ ; $T_j = 125 \text{ }^\circ\text{C}$	0.25	0.4	-	V
$V_{RG}$	gate reverse voltage	$I_{RG} = 2 \text{ mA}$	10	-	-	V
$I_L$	latching current	$I_T = 0.1 \text{ A}$ ; $R_{GK} = 1 \text{ k}\Omega$ ; $T_j = 25 \text{ }^\circ\text{C}$	-	-	6	mA
$I_H$	holding current	$V_D = 12 \text{ V}$ ; $R_{GK} = 1 \text{ k}\Omega$ ; $T_j = 25 \text{ }^\circ\text{C}$	-	-	5	mA
$V_T$	on-state voltage	$I_T = 1.25 \text{ A}$ ; $T_j = 25 \text{ }^\circ\text{C}$	-	-	1.3	V
$I_D$	off-state current	$V_D = V_{DRM} / V_{RRM}$ ; $R_{GK} = 1 \text{ k}\Omega$				$T_j = 25 \text{ }^\circ\text{C}$
$I_R$	reverse current					$T_j = 125 \text{ }^\circ\text{C}$
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 838 \text{ V}$ ; $T_j = 125 \text{ }^\circ\text{C}$ ; $R_{GK} = 1 \text{ k}\Omega$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform	200	-	-	$\text{V}/\mu\text{s}$

Table 4. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th}$	thermal resistance	junction to lead	TO92	-	-	40	K/W
		junction to case	SOT223	-	-	14	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	TO92	-	130	-	K/W
			SOT223	-	120	-	K/W

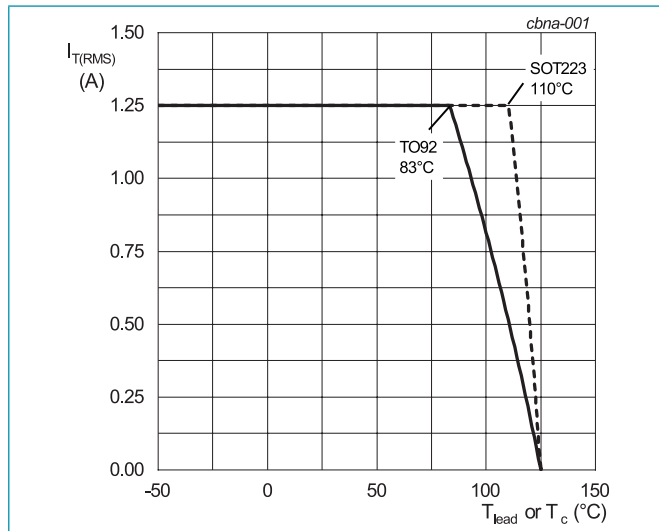


Fig. 1. RMS on-state current as a function of case temperature; maximum values (TO92 / SOT223)

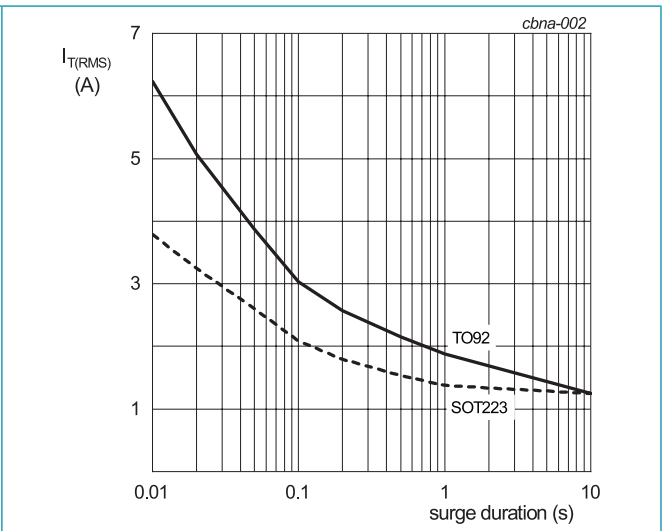


Fig. 2. RMS on-state current as a function of surge duration; maximum values (TO92 / SOT223)  
 $f = 50 \text{ Hz}; T_{lead} = 83 \text{ °C} / T_c = 110 \text{ °C}$

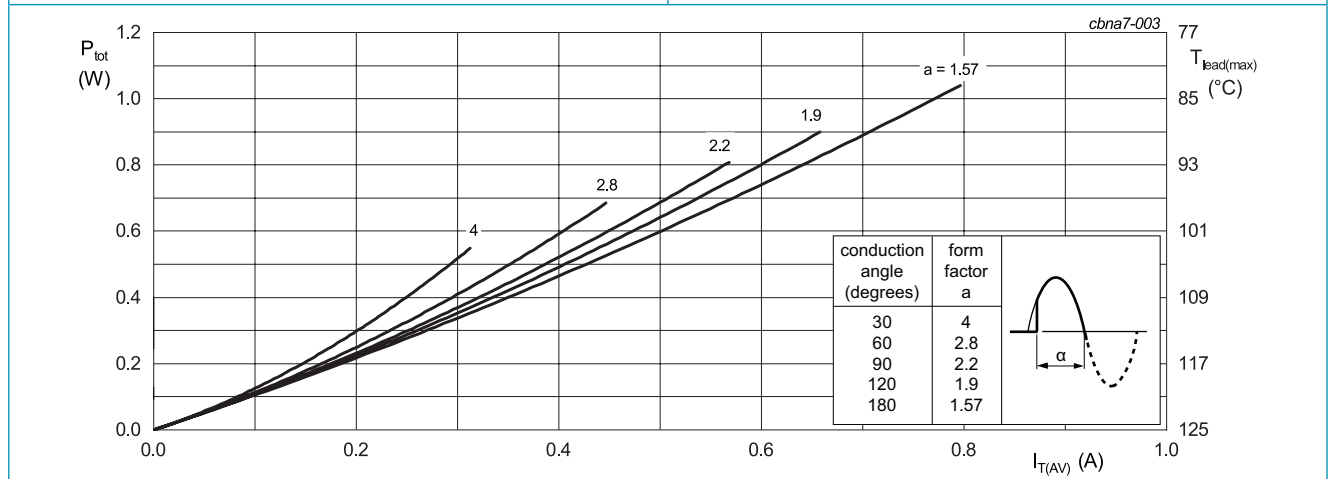
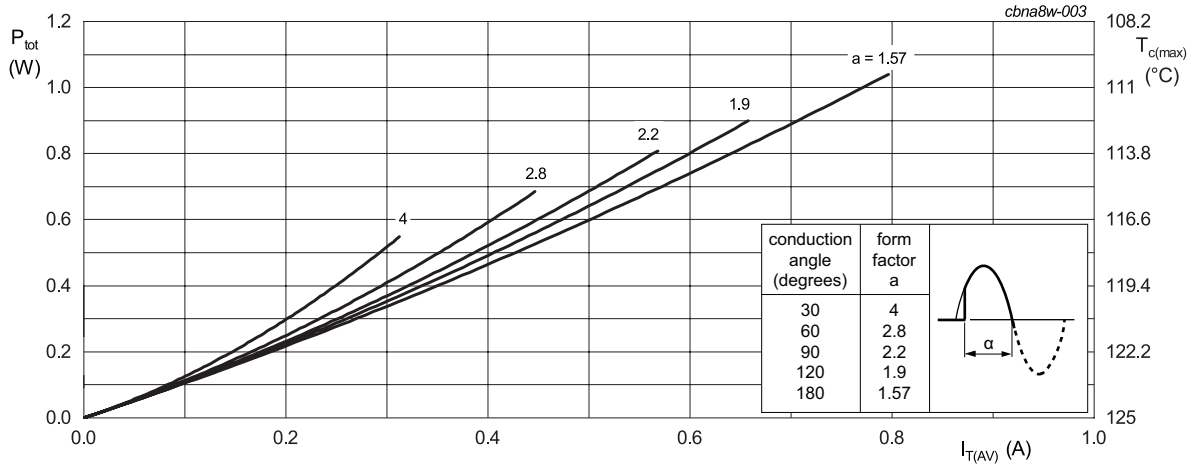
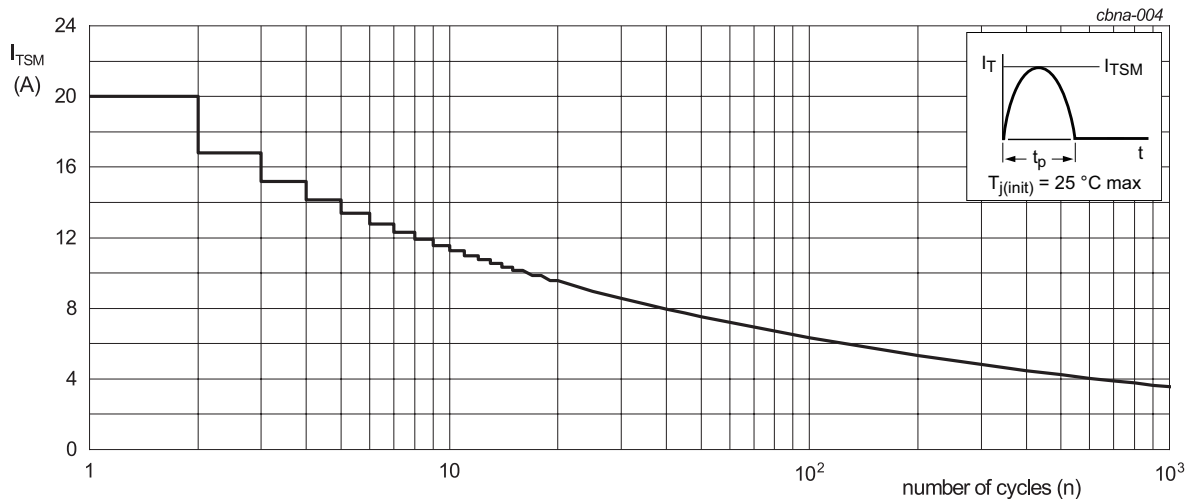


Fig. 3.1. Total power dissipation as a function of RMS on-state current; maximum values (TO92)  
 $\alpha = \text{conduction angle}$   
 $a = \text{form factor} = I_{T(RMS)} / I_{T(AV)}$



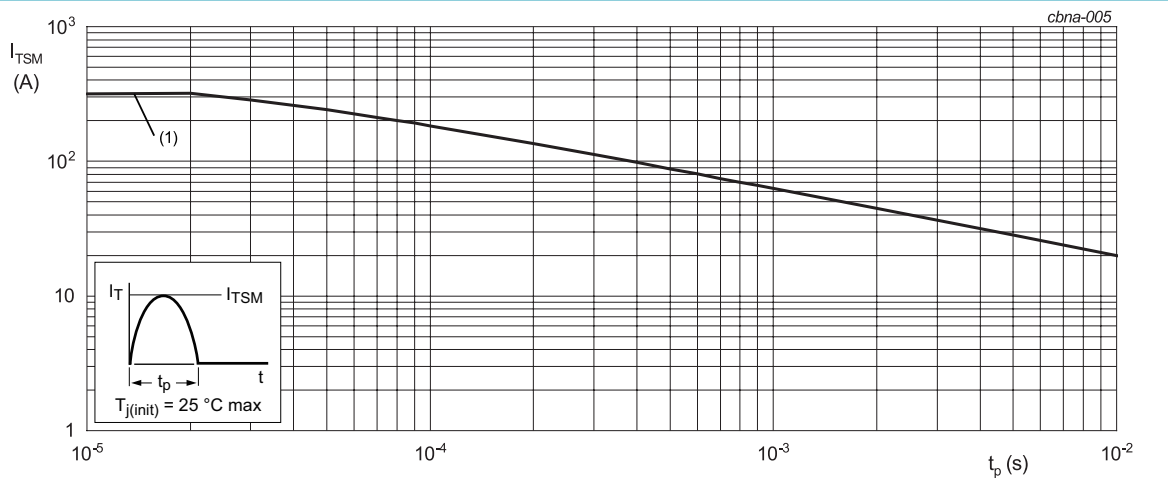
$\alpha$  = conduction angle  
 $a$  = form factor =  $I_{T(RMS)} / I_{T(AV)}$

Fig. 3.2. Total power dissipation as a function of RMS on-state current; maximum values (SOT223)



f = 50 Hz

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



$t_p \leq 10$  ms  
 (1)  $di_T/dt$  limit

Fig. 5. Non-repetitive peak on-state current as a function of pulse duration; maximum values

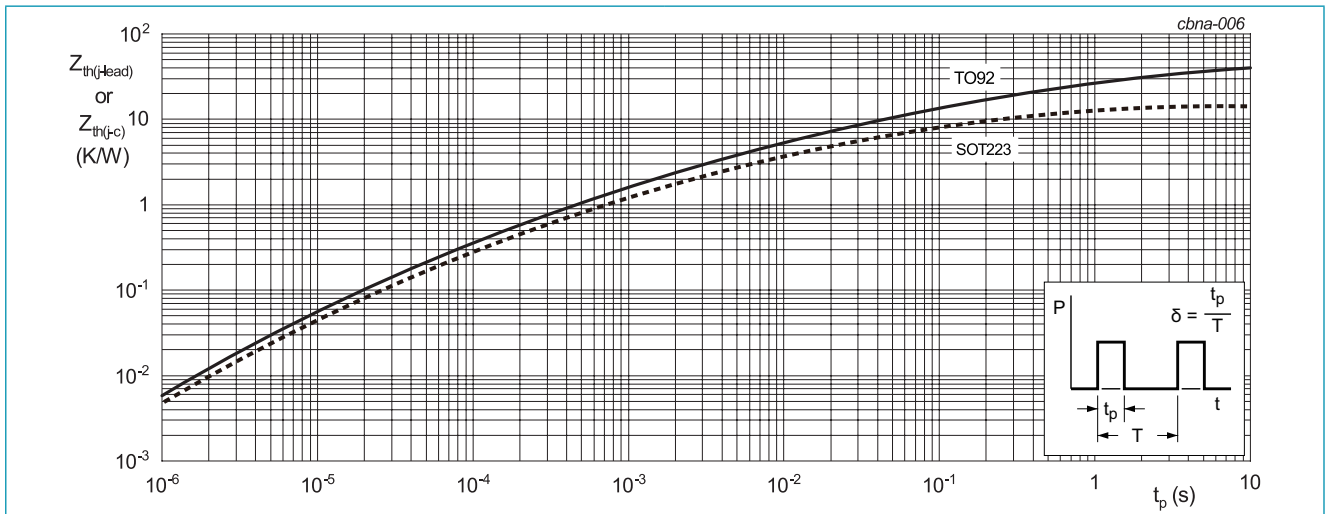


Fig. 6. Transient thermal impedance from junction to lead/case as a function of pulse duration (TO92 / SOT223)

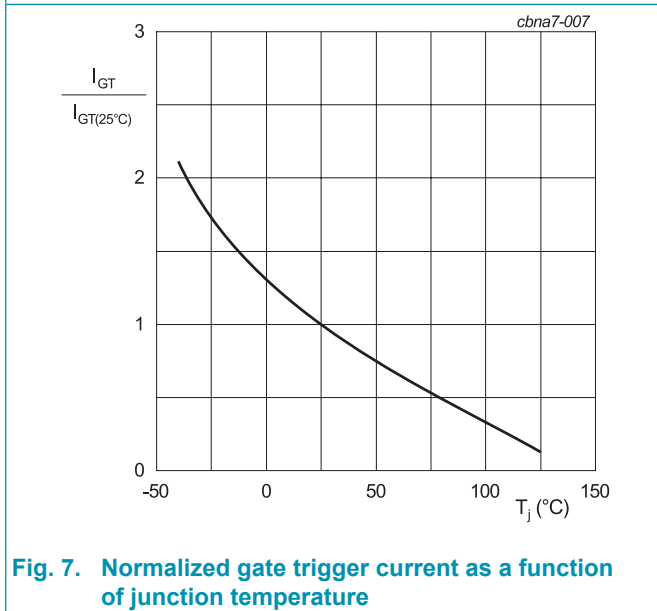


Fig. 7. Normalized gate trigger current as a function of junction temperature

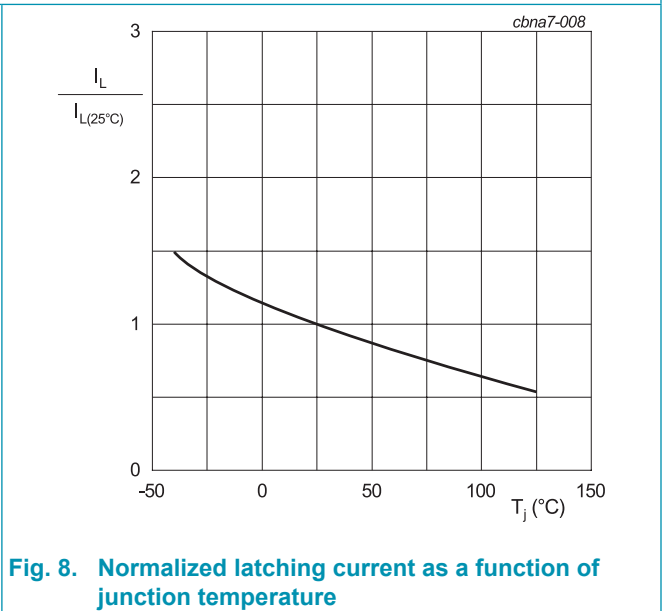


Fig. 8. Normalized latching current as a function of junction temperature

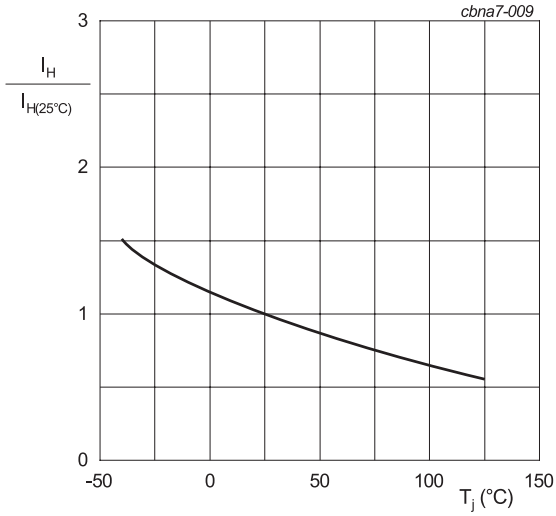


Fig. 9. Normalized holding current as a function of junction temperature

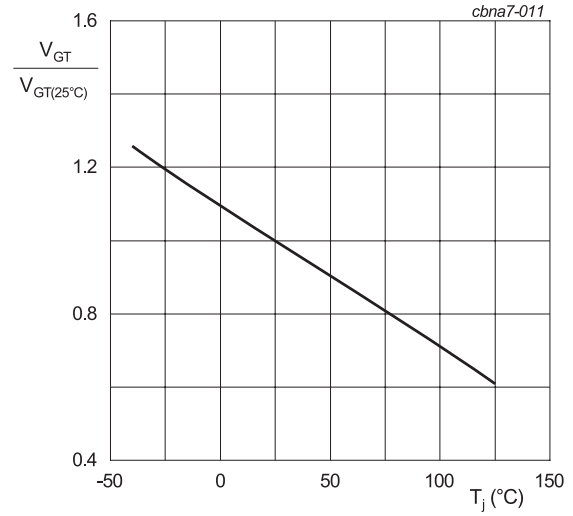
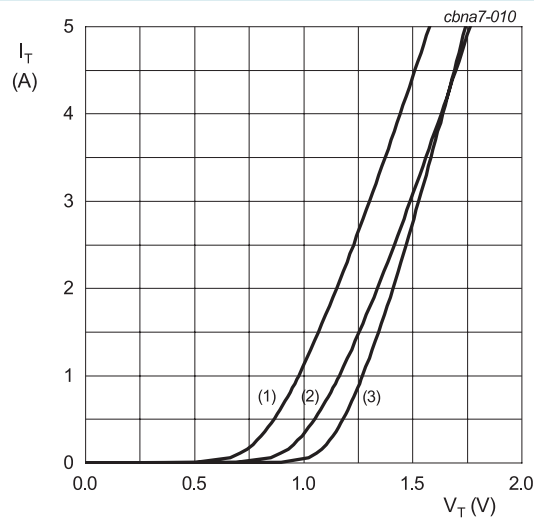


Fig. 10. Normalized gate trigger voltage as a function of junction temperature



$V_o = 1.016 \text{ V}; R_s = 0.1479 \ \Omega$

- (1)  $T_j = 150 \ ^\circ\text{C}$ ; typical values
- (2)  $T_j = 150 \ ^\circ\text{C}$ ; maximum values
- (3)  $T_j = 25 \ ^\circ\text{C}$ ; maximum values

Fig. 11. On-state current as a function of on-state voltage

## 6. Ordering information

Table 5. Ordering information

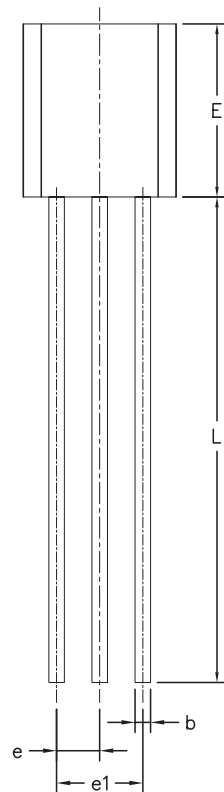
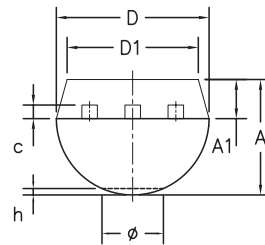
Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WCR03-12M	TO92	WCR03-12MEP	Bulk	1000	TO92L	02-Nov-2019
WCR03-12WM	SOT223	WCR03-12WMX	Reel	1000	SOT223	16-Mar-2006

## 7. Marking

Table 6. Marking codes

Type number	Marking codes
WCR03-12M	WCR03M
WCR03-12WM	WCR03-12M

### 8. Package outline

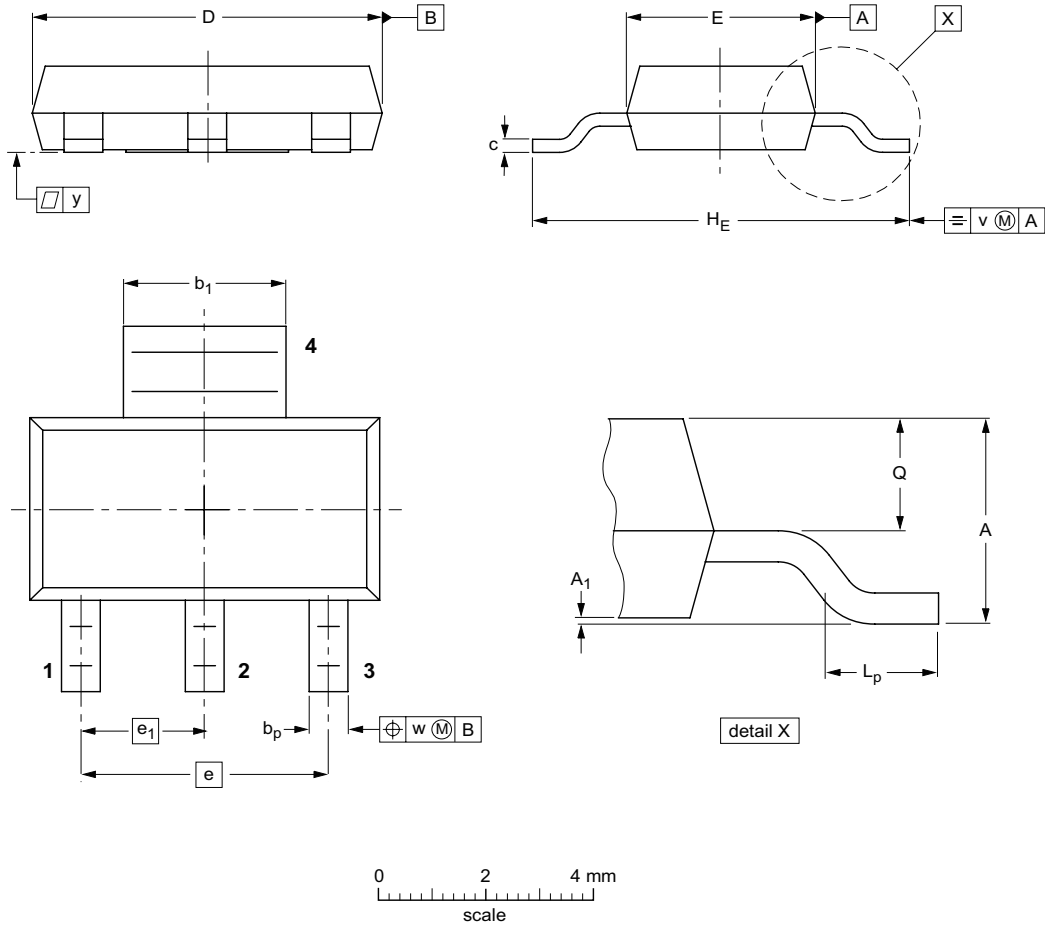


UNIT	A	A1	b	c	D	D1	E	e	e1	L	h	$\phi$
mm	3.30	1.10	0.36	0.28	4.30	3.43	4.30	1.27	2.54	14.10	0.00	1.60
	3.70	1.40	0.56	0.51	4.70		4.70					



Plastic surface-mounted package with increased heatsink; 4 leads

SOT223



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	b <sub>p</sub>	b <sub>1</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w	y
mm	1.8 1.5	0.10 0.01	0.80 0.60	3.1 2.9	0.32 0.22	6.7 6.3	3.7 3.3	4.6	2.3	7.3 6.7	1.1 0.7	0.95 0.85	0.2	0.1	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT223			SC-73			04-11-10 06-03-16

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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